

Silicon NPN Power Transistors

BUV70

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- Fast switching speed
- Wide area of safe operation

APPLICATIONS

- For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

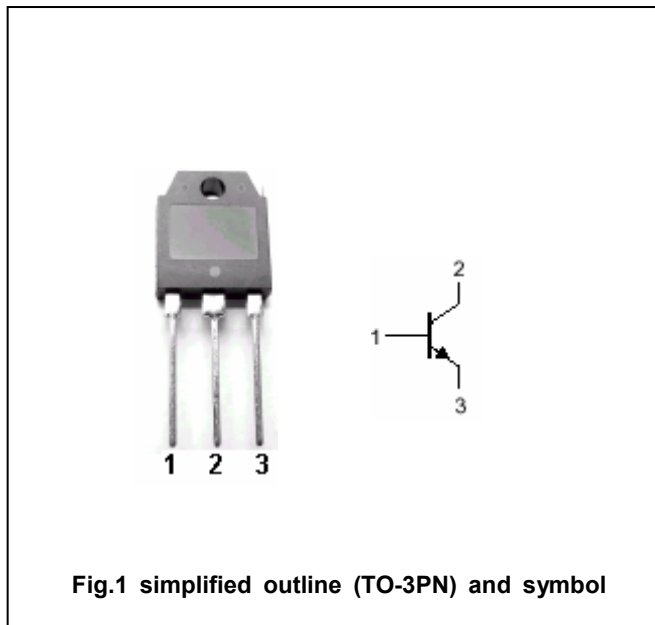


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1300	V
V _{CEO}	Collector-emitter voltage	Open base	550	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
I _B	Base current		4	A
P _C	Collector power dissipation	T _C =25°C	140	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; I _B =0	550			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.2A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =3.2A ; V _{CE} =2V	5			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		9		MHz

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PACKAGE OUTLINE

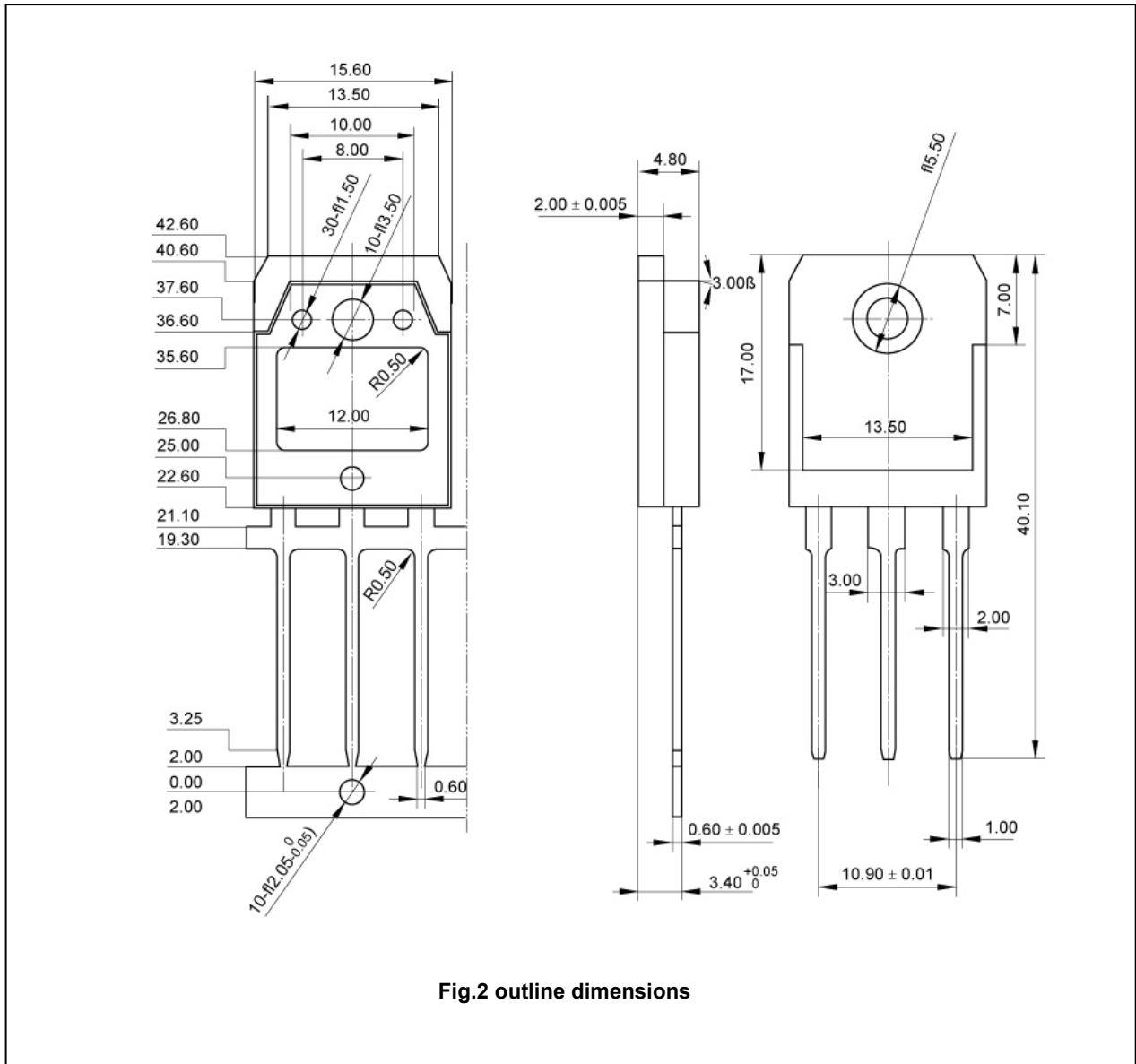


Fig.2 outline dimensions